

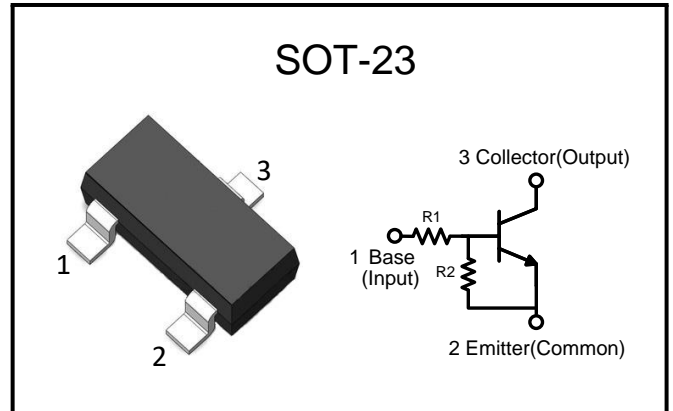
KRC106S

NPN Digital Transistor

Features

- for switching
- interface circuit
- drive circuit applications

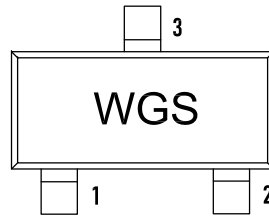
Package



Resistor Values/Marking Code

Type	R1 (K)	R2 (K)	Marking
KRC106S	4.7	47	WGS

Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
KRC106S	SOT-23	WGS	3K	Tape and reel

Absolute Maximum Ratings (@T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector Base Voltage	50	V
V _{CEO}	Collector Emitter Voltage	50	V
I _C	Collector Current	100	mA
P _{tot}	Total Power Dissipation	200	mW
T _J	Operating Junction	150	°C
T _{stg}	Storage Temperature Range	-55 to + 150	°C



KRC106S

NPN Digital Transistor

Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise noted

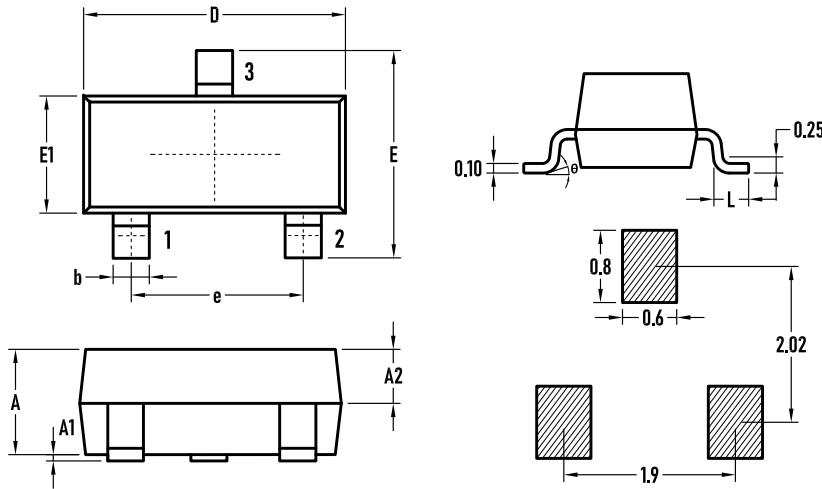
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
h_{FE}	DC Current Gain	$V_{CE} = 10V, I_C=5mA$	80	–	–	
I_{CBO}	Collector Base Cutoff Current	$V_{CB} = 50V$	–	–	100	nA
I_{CEO}	Collector Emitter Cutoff Current	$V_{CE} = 50V$	–	–	500	nA
I_{EBO}	Emitter Base Cutoff Current	$V_{EB} = 6V$	–	–	0.18	mA
$V_{CBO(BR)}$	Collector Base Breakdown Voltage	$I_C = 10\mu A$	50	–	–	V
$V_{CEO(BR)}$	Collector Emitter Breakdown Voltage	$I_C = 2mA$	50	–	–	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C = 10mA, I_B = 0.3mA$	–	–	0.25	V
		$I_C = 10mA, I_B = 5mA$	–	–	0.25	
		$I_C = 10mA, I_B = 1mA$	–	–	0.25	
V_{OL}	Output Voltage (on)	$V_{CC} = 5V, V_B = 2.5V, R_L = 1K\Omega$	–	–	0.2	V
		$V_{CC} = 5V, V_B = 3.5V, R_L = 1K\Omega$	–	–	0.2	
		$V_{CC} = 5V, V_B = 5V, R_L = 1K\Omega$	–	–	0.2	
V_{OH}	Output Voltage (off)	$V_{CC} = 5V, V_B = 0.5V, R_L = 1K\Omega$	4.9	–	–	V
		$V_{CC} = 5V, V_B = 0.05V, R_L = 1K\Omega$	4.9	–	–	
		$V_{CC} = 5V, V_B = 0.25V, R_L = 1K\Omega$	4.9	–	–	
R_1	Input Resistor	–	15.4	–	28.6	K Ω
R_1/R_2	Resistor Ratio	–	0.055	–	0.185	–



KRC106S

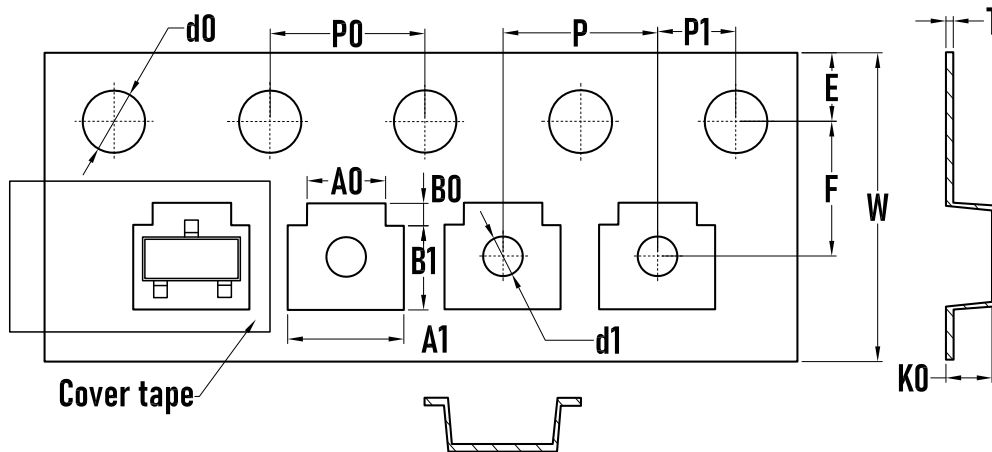
NPN Digital Transistor

Outline Drawing - SOT-23



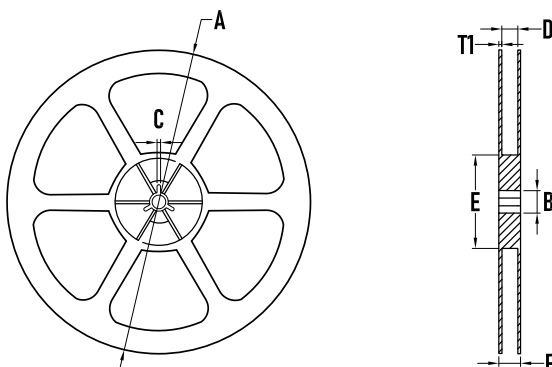
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.95	1.00	—
A1	0.02	0.06	0.10
A2	—	0.60	—
D	2.85	2.90	2.95
b	0.37	0.40	0.43
E	2.35	2.40	2.45
E1	1.25	1.30	1.35
e	1.85	1.90	1.95
L	0.35	0.40	0.48
θ	0	—	6°

Packaging Tape - SOT-23



SYMBOL	MILLIMETER
A0	2.10±0.10
A1	3.10±0.10
B0	0.65±0.10
B1	2.75±0.10
d0	1.55±0.10
d1	1.00±0.05
E	1.75±0.10
F	3.50±0.10
K0	1.10±0.10
P	4.00±0.10
P0	4.00±0.10
P1	2.00±0.10
W	8.00±0.30
T	0.20 ±0.05

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	3.1
C	13.50
D	9.6±0.3
E	75±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

**BORN SEMICONDUCTOR, INC. ALL
RIGHT RESERVED**

Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

Revision: 2022-Jan-1-A



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - Pre-Biased](#) category:

Click to view products by [Bourne](#) manufacturer:

Other Similar products are found below :

[DRC9A14E0L](#) [DTA124GKAT146](#) [DTA144WETL](#) [DTA144WKAT146](#) [DTC113EET1G](#) [DTC115TETL](#) [DTC115TKAT146](#)
[DTC144VUAT106](#) [MUN5241T1G](#) [BCR158WH6327XTSA1](#) [NSBA114TDP6T5G](#) [SMUN5330DW1T1G](#) [SSVMUN5312DW1T2G](#)
[RN1303\(TE85L,F\)](#) [RN1306\(TE85L,F\)](#) [EMH15T2R](#) [SMUN2214T3G](#) [SMUN5335DW1T1G](#) [NSBC143ZPDP6T5G](#) [NSVDTA143ZET1G](#)
[SMUN2214T1G](#) [FMA7AT148](#) [DTC114EUA-TP](#) [SMUN5237DW1T1G](#) [SMUN5213DW1T1G](#) [SMUN5114DW1T1G](#) [SMUN2111T1G](#)
[DTC124ECA-TP](#) [DTA114ECA-TP](#) [DTC113EM3T5G](#) [NSVMUN5135DW1T1G](#) [NSVMUN2237T1G](#) [NSVDTC143ZM3T5G](#)
[SMUN5335DW1T2G](#) [SMUN5216DW1T1G](#) [NSVMUN5316DW1T1G](#) [NSVMUN5215DW1T1G](#) [NSVMUN5213DW1T3G](#)
[NSVMUN2112T1G](#) [NSVIMD10AMT1G](#) [NSVEMC2DXV5T1G](#) [NSVDTC144WET1G](#) [NSVDTC123JET1G](#) [NSVDTA143EM3T5G](#)
[NSVB1706DMW5T1G](#) [NSBC143EDP6T5G](#) [RN2101,LF\(CT](#) [NSBA144WDXV6T1G](#) [DTA115TET1G](#) [NSBC115TDP6T5G](#)